

# Citations for Target : **GaP**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1972</b>	Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: II: Range Distributions Derived from Collection and Sputter-Etch Curves.' <i>Rad. Effects, 16, 107-114 (1972)</i> <i>Comment : R. 10-30 keV Kr, Tl -&gt; GaAs, GaP, Ge, Si</i>	<b>1972-Cart</b> 0976
<b>1972</b>	Whitton, J. L. Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: I Saturation Effects.' <i>Rad. Effects, 16, 101-105 (1972)</i> <i>Comment : R, dR. 10-30 keV Kr, Tl -&gt; Si, Ge, GaP, GaAs</i>	<b>1972-Whit</b> 0975
<b>1975</b>	Thompson, D. A. Johar, S. S. Shewchun, J. 'Nitrogen Implantation into GaP: Damage and Nitrogen Location Studies' <i>J. Elec. Mater., 4, 195-207 (1975)</i> <i>Comment : R. 40, 80 keV N -&gt; GaP</i>	<b>1975-Thom</b> 1020
<b>1976</b>	Kachare, A. H. Spitzer, W. G. Fredrickson, J. E. Euler, F. K. 'Measurements of Layer Thicknesses and Refractive Indices in High Energy Ion Implanted GaAs and GaP' <i>J. Appl. Phys., 47, 5347-5381 (1976)</i> <i>Comment : R. N, P (3 MeV) -&gt; GaAs, GaP</i>	<b>1976-Kach</b> 2149
<b>1980</b>	Revesz, P. Farkas, Gy. Gyulai, J. 'Behavior of Antimony Above Solid Solubility in Silicon Produced by Implantation and Laser Annealing' <i>Rad. Effects, 47, 149-152 (1980)</i> <i>Comment : R, dR. .5-2 MeV Ni -&gt; GaP</i>	<b>1980-Reve</b> 1329
<b>1984</b>	Khodyrev, V. A. Mizgulin, V. N. Sirotnin, E. I. Tulinov, A. F. 'Stopping Cross Sections of 80-500 keV Protons in Phosphorus Compounds' <i>Rad. Effects, 83, 21-37 (1984)</i> <i>Comment : S. H (80-500 keV) -&gt; InP, GaP, ZnSiP2</i>	<b>1984-Khod</b> 1690